

**General Description**

- Trench Power AlphaMOS-II technology
- Low  $R_{DS(ON)}$
- Low  $C_{iss}$  and  $C_{rss}$
- High Current Capability
- RoHS and Halogen Free Compliant

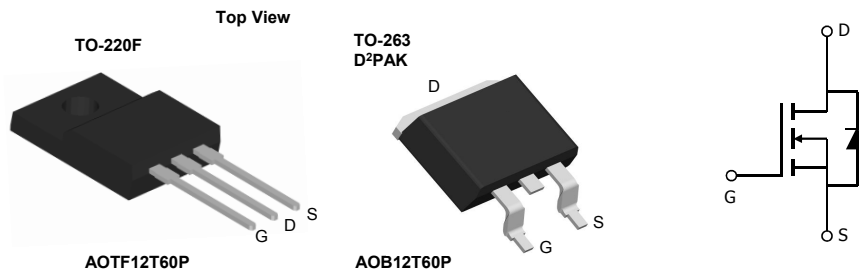
**Applications**

- General Lighting for LED and CCFL
- AC/DC Power supplies for Industrial, Consumer, and Telecom

**Product Summary**

$V_{DS} @ T_{j,max}$	700V
$I_{DM}$	48A
$R_{DS(ON),max}$	< 0.52Ω
$Q_{g,typ}$	33nC
$E_{oss} @ 400V$	4.4μJ

100% UIS Tested  
100%  $R_g$  Tested



Orderable Part Number	Package Type	Form	Minimum Order Quantity
AOB12T60PL	TO-263 Green	Tape & Reel	800
AOTF12T60P	TO-220F Pb Free	Tube	1000

**Absolute Maximum Ratings  $T_A=25^{\circ}C$  unless otherwise noted**

Parameter	Symbol	AOB12T60P	AOTF12T60P	Units
Drain-Source Voltage	$V_{DS}$	600		V
Gate-Source Voltage	$V_{GS}$	±30		V
Continuous Drain Current	$I_D$	$T_C=25^{\circ}C$	12	12*
		$T_C=100^{\circ}C$	9	9*
Pulsed Drain Current <sup>C</sup>	$I_{DM}$	48		A
Avalanche Current <sup>C</sup> L=1mH	$I_{AR}$	12		A
Repetitive avalanche energy <sup>C</sup>	$E_{AR}$	72		mJ
Single pulsed avalanche energy <sup>G</sup>	$E_{AS}$	750		mJ
MOSFET dv/dt ruggedness	dv/dt	50		V/ns
Peak diode recovery dv/dt <sup>J</sup>		15		
Power Dissipation <sup>B</sup>	$P_D$	$T_C=25^{\circ}C$	250	50
		Derate above 25°C	2	0.4
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150		°C
Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds	$T_L$	300		°C

**Thermal Characteristics**

Parameter	Symbol	AOB12T60P	AOTF12T60P	Units
Maximum Junction-to-Ambient <sup>A,D</sup>	$R_{\theta JA}$	65	65	°C/W
Maximum Case-to-sink <sup>A</sup>	$R_{\theta CS}$	0.5	--	°C/W
Maximum Junction-to-Case	$R_{\theta JC}$	0.5	2.5	°C/W

\* Drain current limited by maximum junction temperature.



Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	600			V
		I <sub>D</sub> =250μA, V <sub>GS</sub> =0V, T <sub>J</sub> =150°C		700		
BV <sub>DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V		0.58		V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =600V, V <sub>GS</sub> =0V			1	μA
		V <sub>DS</sub> =480V, T <sub>J</sub> =125°C			10	
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±30V			±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =5V, I <sub>D</sub> =250μA	3	4.1	5	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =6A		0.44	0.52	Ω
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =40V, I <sub>D</sub> =6A		11		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1A, V <sub>GS</sub> =0V		0.73	1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current				12	A
I <sub>SM</sub>	Maximum Body-Diode Pulsed Current <sup>C</sup>				48	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =100V, f=1MHz		2028		pF
C <sub>oss</sub>	Output Capacitance				71	
C <sub>o(er)</sub>	Effective output capacitance, energy related <sup>H</sup>	V <sub>GS</sub> =0V, V <sub>DS</sub> =0 to 480V, f=1MHz		52		pF
C <sub>o(tr)</sub>	Effective output capacitance, time related <sup>I</sup>				94	
C <sub>rss</sub>	Reverse Transfer Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =100V, f=1MHz		13		pF
R <sub>g</sub>	Gate resistance	f=1MHz		2.2		Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g</sub>	Total Gate Charge	V <sub>GS</sub> =10V, V <sub>DS</sub> =480V, I <sub>D</sub> =12A		33	50	nC
Q <sub>gs</sub>	Gate Source Charge			13		nC
Q <sub>gd</sub>	Gate Drain Charge			10		nC
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> =10V, V <sub>DS</sub> =300V, I <sub>D</sub> =12A, R <sub>G</sub> =25Ω		52		ns
t <sub>r</sub>	Turn-On Rise Time			72		ns
t <sub>D(off)</sub>	Turn-Off DelayTime			66		ns
t <sub>f</sub>	Turn-Off Fall Time			42		ns
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =12A, di/dt=100A/μs, V <sub>DS</sub> =100V		483		ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =12A, di/dt=100A/μs, V <sub>DS</sub> =100V		7		μC

A. The value of R<sub>θJA</sub> is measured with the device in a still air environment with T<sub>A</sub>=25° C.

B. The power dissipation P<sub>D</sub> is based on T<sub>J(MAX)</sub>=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150° C, Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub>=25° C.

D. The R<sub>θJA</sub> is the sum of the thermal impedance from junction to case R<sub>θJC</sub> and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300 ms pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T<sub>J(MAX)</sub>=150° C. The SOA curve provides a single pulse rating.

G. L=60mH, I<sub>AS</sub>=5A, V<sub>DD</sub>=150V, R<sub>G</sub>=25Ω, Starting T<sub>J</sub>=25° C.

H. C<sub>o(er)</sub> is a fixed capacitance that gives the same stored energy as C<sub>oss</sub> while V<sub>DS</sub> is rising from 0 to 80% V<sub>(BR)DSS</sub>.

I. C<sub>o(tr)</sub> is a fixed capacitance that gives the same charging time as C<sub>oss</sub> while V<sub>DS</sub> is rising from 0 to 80% V<sub>(BR)DSS</sub>.

J. I<sub>SD</sub>≤I<sub>D</sub>, di/dt≤200A/μs, V<sub>DD</sub>=400V, T<sub>J</sub>≤T<sub>J(MAX)</sub>.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

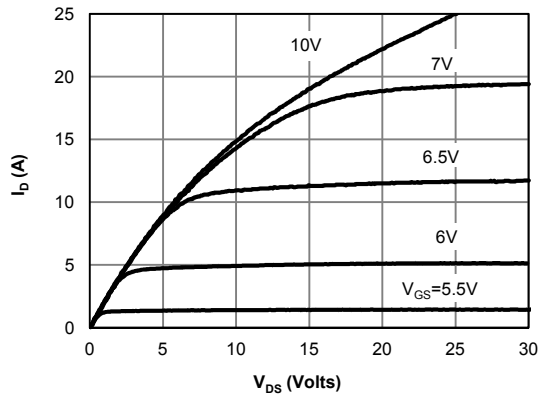


Figure 1: On-Region Characteristics

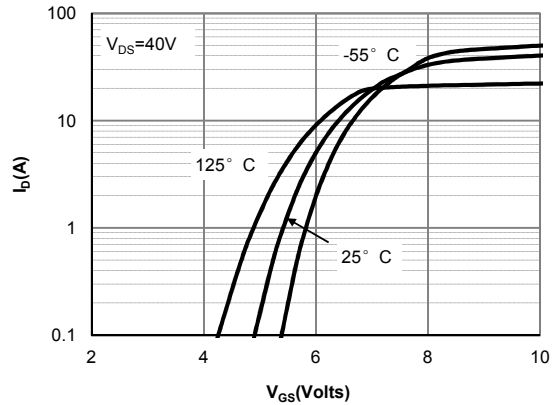


Figure 2: Transfer Characteristics

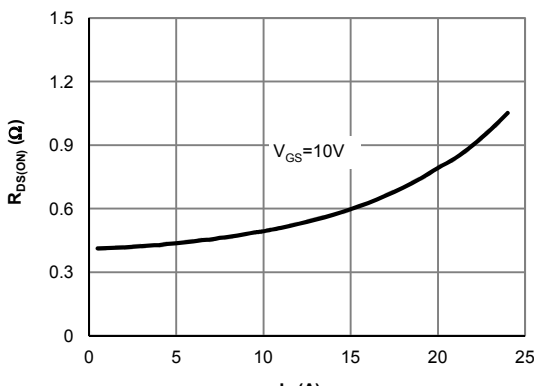


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

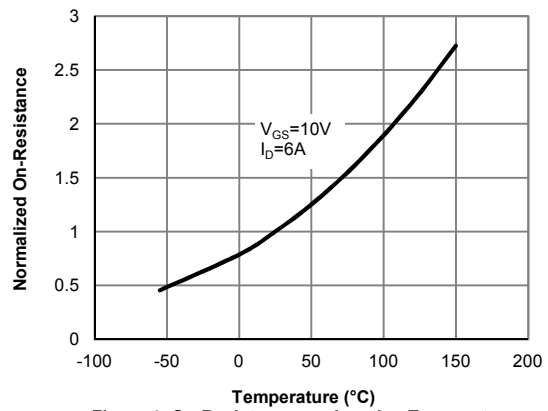


Figure 4: On-Resistance vs. Junction Temperature

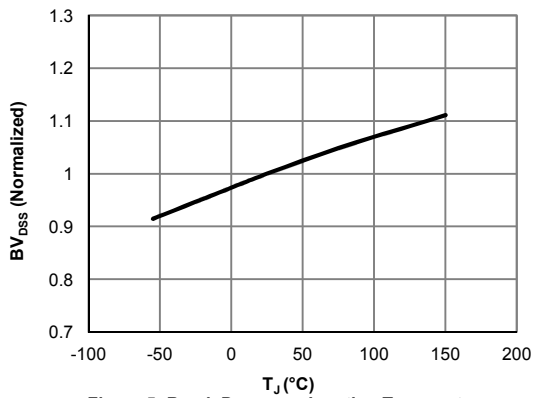


Figure 5: Break Down vs. Junction Temperature

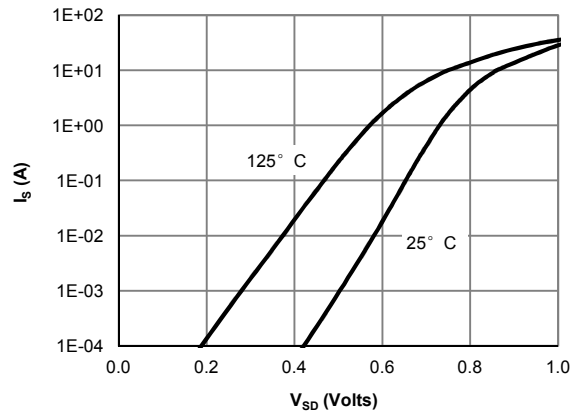


Figure 6: Body-Diode Characteristics



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

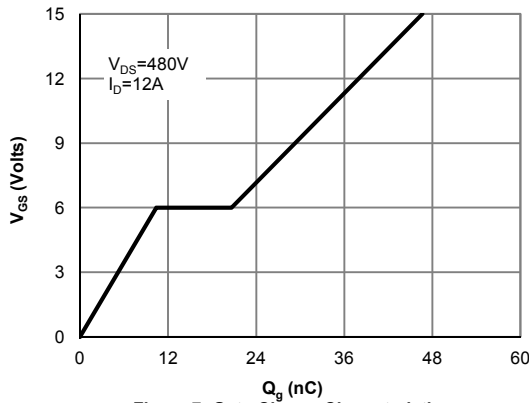


Figure 7: Gate-Charge Characteristics

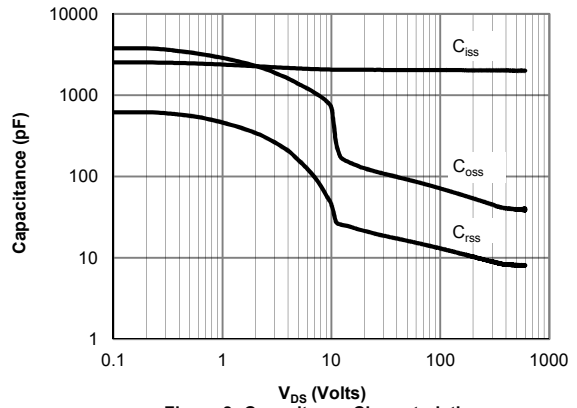


Figure 8: Capacitance Characteristics

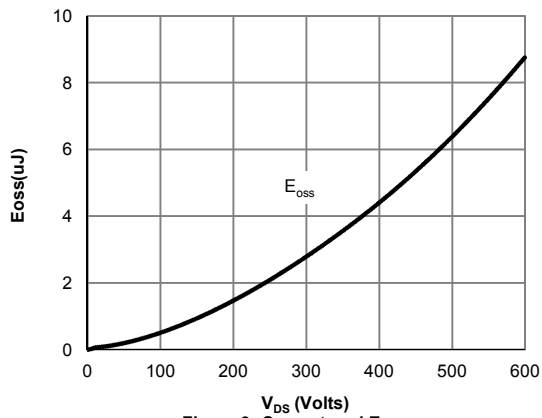


Figure 9: Coss stored Energy

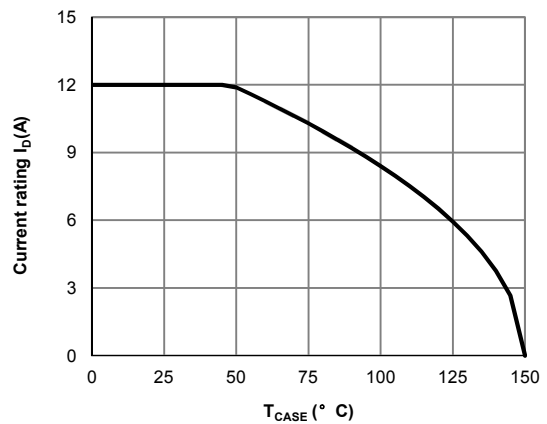


Figure 10: Current De-rating (Note F)

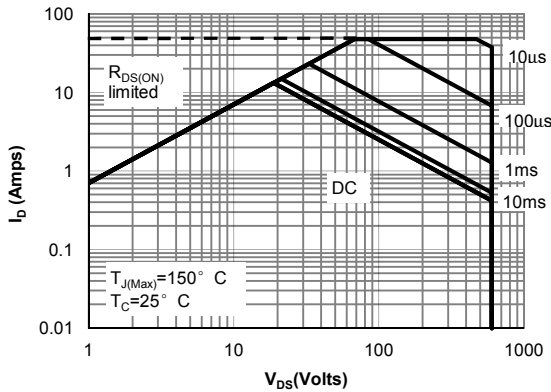


Figure 11: Maximum Forward Biased Safe Operating Area for TO-263 (Note F)

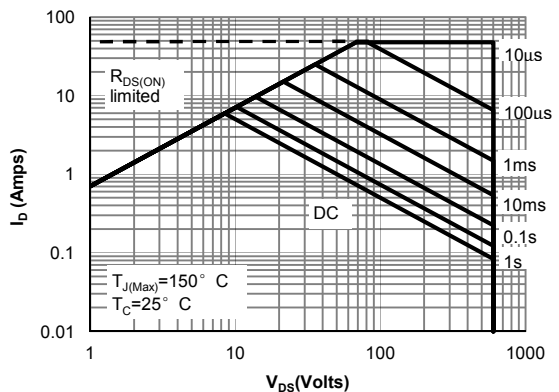


Figure 12: Maximum Forward Biased Safe Operating Area for TO-220F Pb Free (Note F)



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

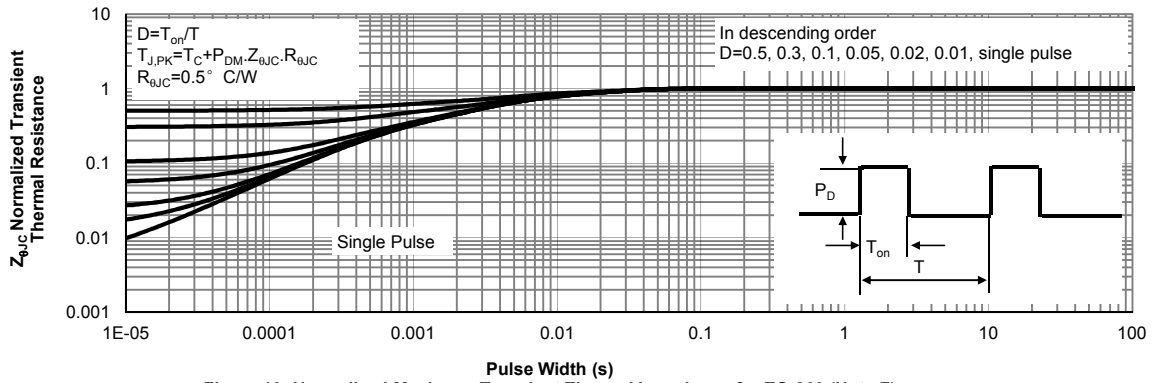


Figure 13: Normalized Maximum Transient Thermal Impedance for TO-263 (Note F)

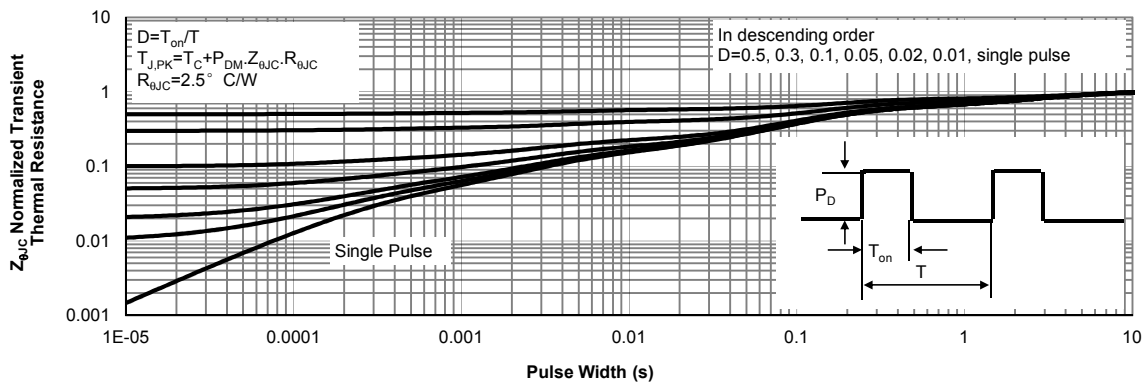
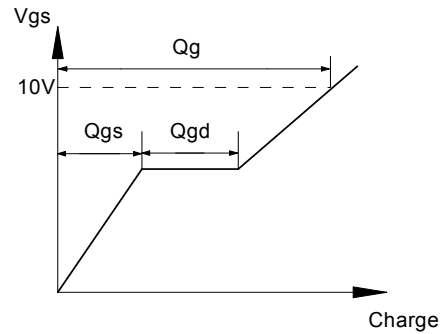
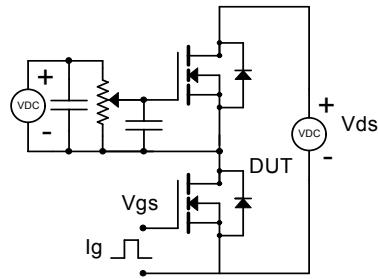
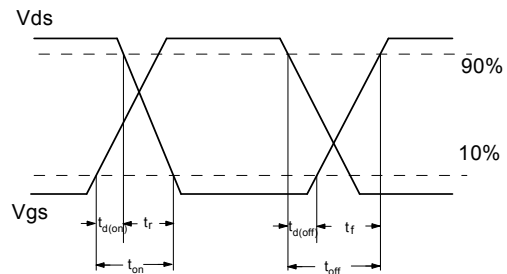
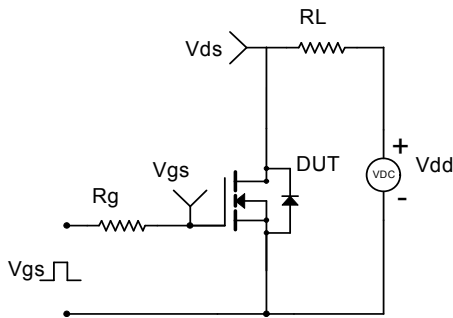


Figure 14: Normalized Maximum Transient Thermal Impedance for TO-220F Pb Free (Note F)

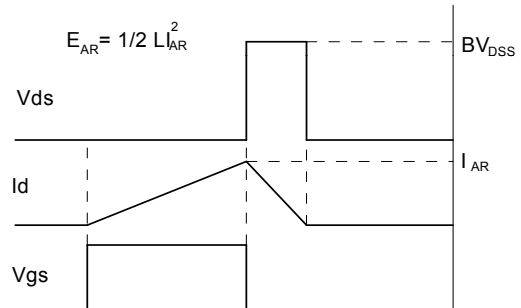
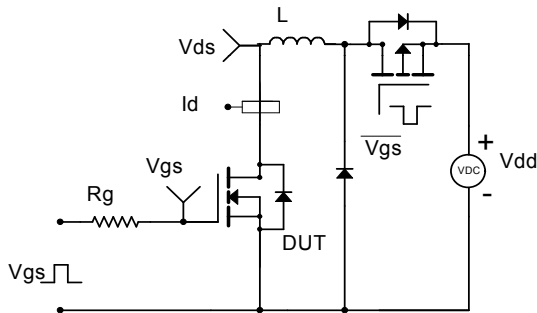
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

